NSN 5961-01-337-8555

Diode Semiconductor Device - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-337-8555
Inclosure Material:
Glass
Overall Length:
Between 0.293 inches and 0.357 inches
Terminal Length:
Between 1.000 inches and 1.625 inches
Overall Diameter:
Between 0.215 inches and 0.235 inches
Function For Which Designed:
Transient suppressor
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
Do-13
Electrode Internally-electrically Connected To Case:
Collector
Mounting Method:
Terminal
Features Provided:
Hermetically sealed case and quality assurance level tx
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
25.2 breakdown voltage, dc
Voltage Tolerance In Percent:
-5.0/ + 5.0
Current Rating Per Characteristic:
5.00 microamperes forward current, average peak
Power Rating Per Characteristic:
1.0 watts small-signal input power, common-collector major
Maximum Operating Tempurature Per Measurement Point:
175.0 degrees celsius junction
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
2 uninsulated wire lead
Specification Data:
81349-mil-s-19500/500 government specification
Shelf Life:
N/a
Unit Of Measure:

No

Demilitarization:

NSN 5961-01-337-8555

Diode Semiconductor Device - Page 2 of 2



Fiig:

A110a0